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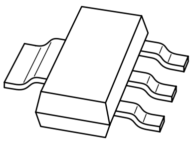


PBSS8110Z

100 V, 1 A NPN low V_{CEsat} (BISS) transistor

Rev. 02 — 8 January 2007 Product data sheet

1. Product profile

1.1 General description

NPN low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a SOT223 (SC-73) small Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS9110Z.

1.2 Features

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

1.3 Applications

- High-voltage DC-to-DC conversion
- High-voltage MOSFET gate driving
- High-voltage motor control
- High-voltage power switches (e.g. motors, fans)
- Automotive applications

1.4 Quick reference data

Table 1. Quick reference data

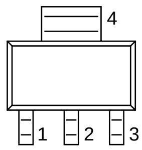
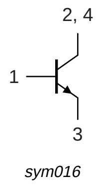
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base		-	-	100	V
I_C	collector current			-	-	1	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms		-	-	3	A
R_{CEsat}	collector-emitter saturation resistance	$I_C = 1$ A; $I_B = 100$ mA	[1]	-	160	200	mΩ

[1] Pulse test: $t_p \leq 300$ µs; $\delta \leq 0.02$.

founded by Philips

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Symbol
1	base		
2	collector		
3	emitter		
4	collector		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS8110Z	SC-73	plastic surface-mounted package with increased heat sink; 4 leads	SOT223

4. Marking

Table 4. Marking codes

Type number	Marking code
PBSS8110Z	PB8110

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	120	V
V_{CEO}	collector-emitter voltage	open base		-	100	V
V_{EBO}	emitter-base voltage	open collector		-	5	V
I_C	collector current			-	1	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms		-	3	A
I_B	base current			-	0.3	A
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1]	-	0.65	W
			[2]	-	1	W
			[3]	-	1.4	W

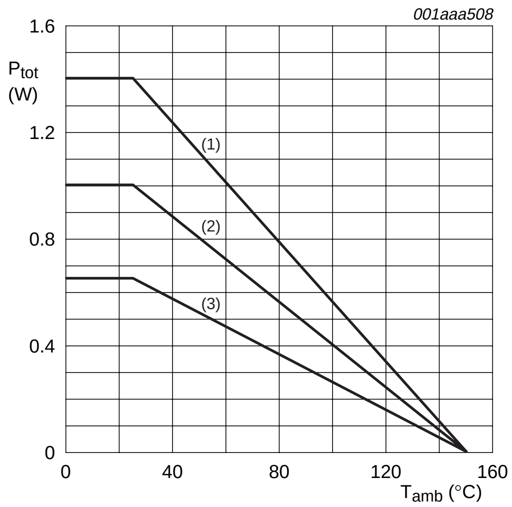
Table 5. Limiting values *...continued*
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
T_j	junction temperature		-	150	°C
T_{amb}	ambient temperature		–65	+150	°C
T_{stg}	storage temperature		–65	+150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm^2.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm^2.



(1) FR4 PCB, mounting pad for collector 6 cm^2

(2) FR4 PCB, mounting pad for collector 1 cm^2

(3) FR4 PCB, standard footprint

Fig 1. Power derating curves

6. Thermal characteristics

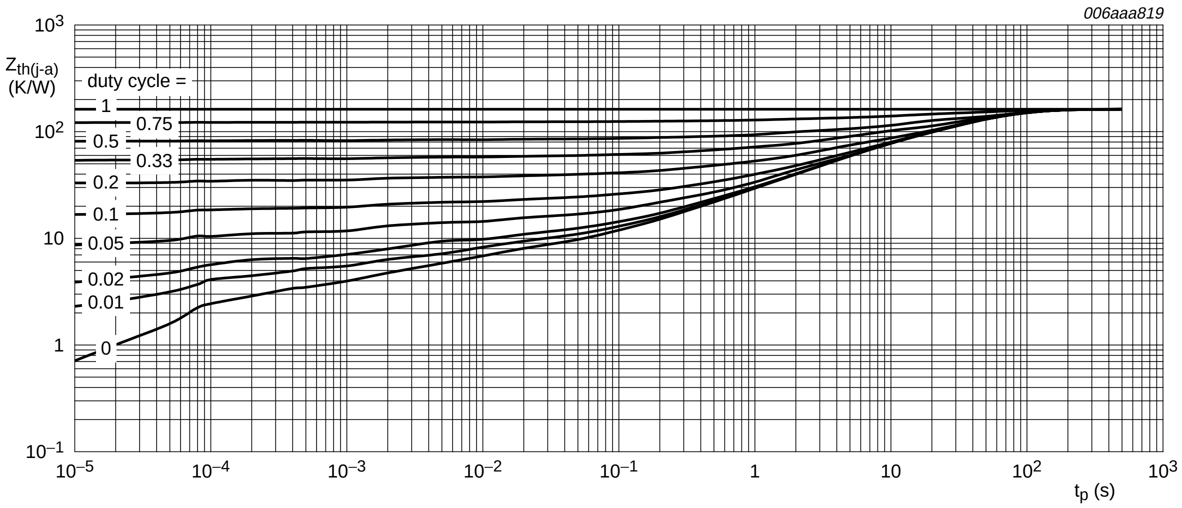
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	192	K/W
			[2]	-	-	125	K/W
			[3]	-	-	89	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	17	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

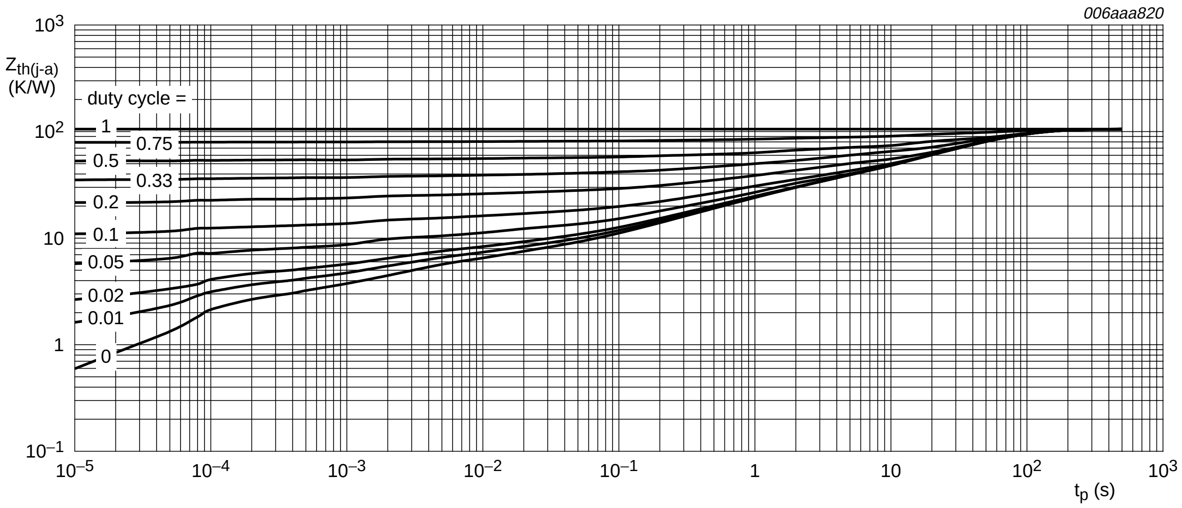
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm^2.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm^2.



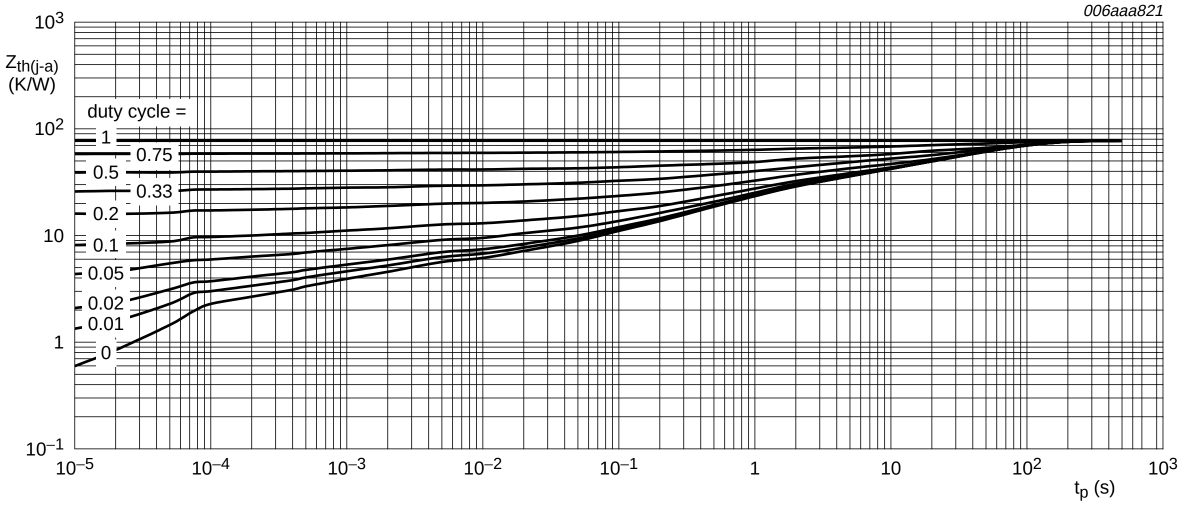
FR4 PCB, standard footprint

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for collector 1 cm^2

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for collector 6 cm^2

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

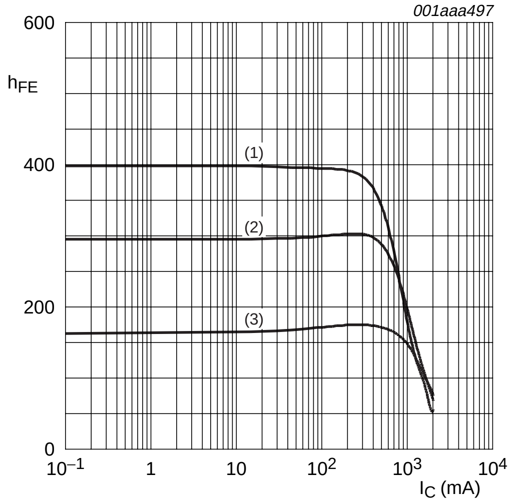
7. Characteristics

Table 7. Characteristics

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	V_{CB} = 80 V; I_E = 0 A		-	-	100	nA
		V_{CB} = 80 V; I_E = 0 A; T_j = 150 °C		-	-	50	µA
I_{CES}	collector-emitter cut-off current	V_{CE} = 80 V; V_{BE} = 0 V		-	-	100	nA
I_{EBO}	emitter-base cut-off current	V_{EB} = 4 V; I_C = 0 A		-	-	100	nA
h_{FE}	DC current gain	V_{CE} = 10 V; I_C = 1 mA		150	-	-	
		V_{CE} = 10 V; I_C = 250 mA		150	-	500	
		V_{CE} = 10 V; I_C = 0.5 A	[1]	100	-	-	
		V_{CE} = 10 V; I_C = 1 A	[1]	80	-	-	
V_{CEsat}	collector-emitter saturation voltage	I_C = 100 mA; I_B = 10 mA		-	-	40	mV
		I_C = 500 mA; I_B = 50 mA	[1]	-	-	120	mV
		I_C = 1 A; I_B = 100 mA	[1]	-	-	200	mV
R_{CEsat}	collector-emitter saturation resistance	I_C = 1 A; I_B = 100 mA	[1]	-	160	200	mΩ
V_{BEsat}	base-emitter saturation voltage	I_C = 1 A; I_B = 100 mA	[1]	-	-	1.05	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = 10 V; I_C = 1 A	[1]	-	-	0.9	V
t_d	delay time	V_{CC} = 10 V; I_C = 0.5 A; I_{Bon} = 0.025 A; I_{Boff} = −0.025 A		-	25	-	ns
t_r	rise time			-	220	-	ns
t_{on}	turn-on time			-	245	-	ns
t_s	storage time			-	365	-	ns
t_f	fall time			-	185	-	ns
t_{off}	turn-off time			-	550	-	ns
f_T	transition frequency	V_{CE} = 10 V; I_C = 50 mA; f = 100 MHz		100	-	-	MHz
C_c	collector capacitance	V_{CB} = 10 V; I_E = i_e = 0 A; f = 1 MHz		-	-	7.5	pF

[1] Pulse test: $t_p \leq 300$ µs; $\delta \leq 0.02$.



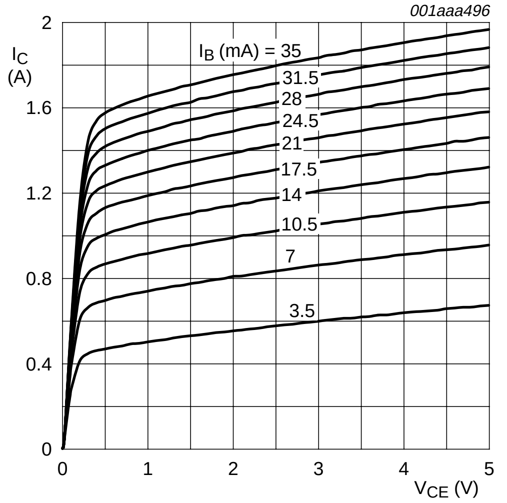
V_{CE} = 10 V

(1) T_{amb} = 100 °C

(2) T_{amb} = 25 °C

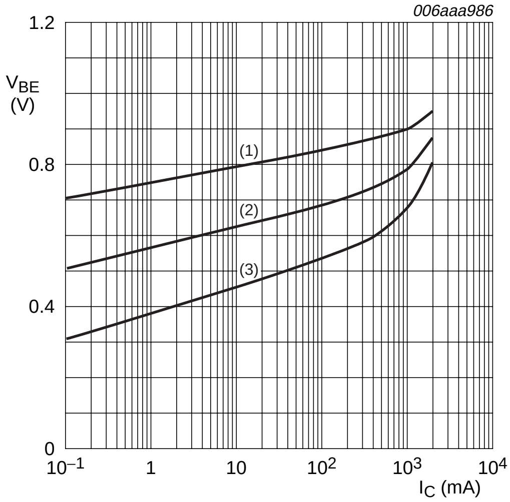
(3) T_{amb} = −55 °C

Fig 5. DC current gain as a function of collector current; typical values



T_{amb} = 25 °C

Fig 6. Collector current as a function of collector-emitter voltage; typical values



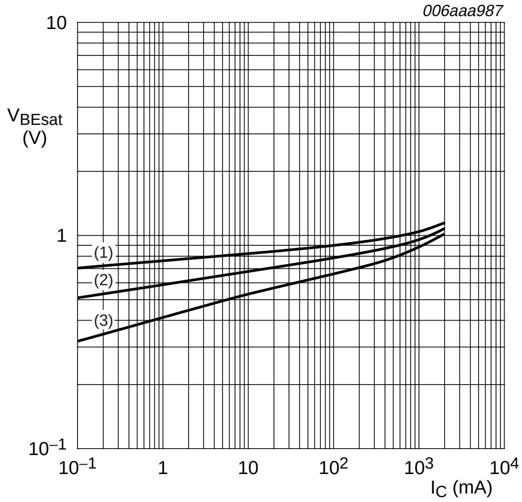
V_{CE} = 10 V

(1) T_{amb} = −55 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C

Fig 7. Base-emitter voltage as a function of collector current; typical values



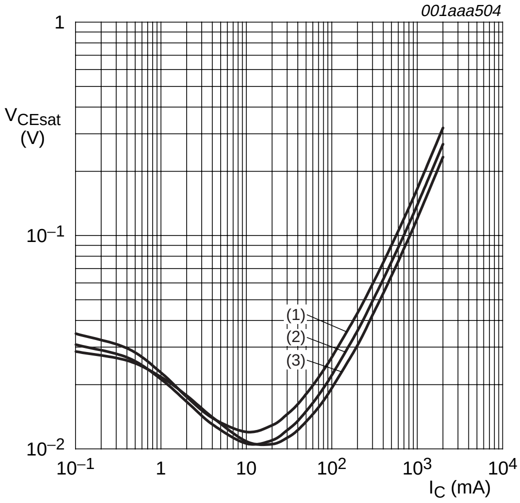
I_C/I_B = 10

(1) T_{amb} = −55 °C

(2) T_{amb} = 25 °C

(3) T_{amb} = 100 °C

Fig 8. Base-emitter saturation voltage as a function of collector current; typical values



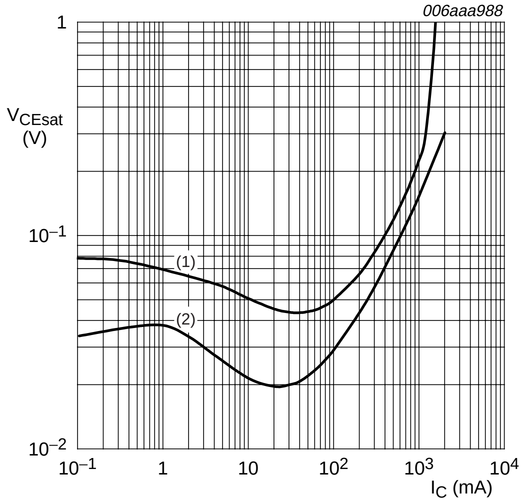
$I_C/I_B = 10$

(1) $T_{amb} = 100$ °C

(2) $T_{amb} = 25$ °C

(3) $T_{amb} = -55$ °C

Fig 9. Collector-emitter saturation voltage as a function of collector current; typical values

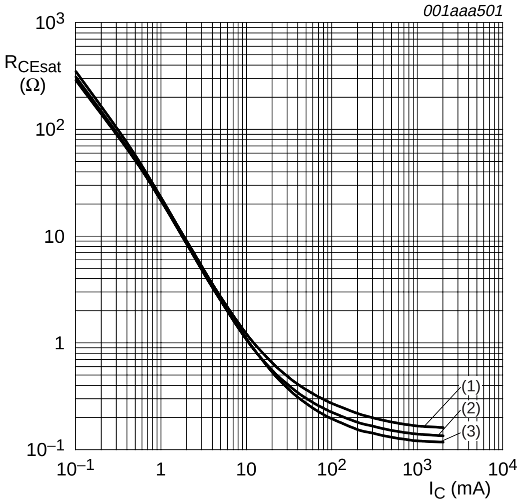


$T_{amb} = 25$ °C

(1) $I_C/I_B = 50$

(2) $I_C/I_B = 20$

Fig 10. Collector-emitter saturation voltage as a function of collector current; typical values



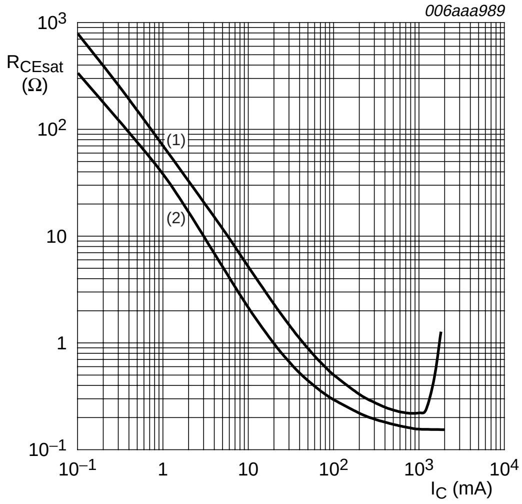
$I_C/I_B = 10$

(1) $T_{amb} = 100$ °C

(2) $T_{amb} = 25$ °C

(3) $T_{amb} = -55$ °C

Fig 11. Collector-emitter saturation resistance as a function of collector current; typical values



$T_{amb} = 25$ °C

(1) $I_C/I_B = 50$

(2) $I_C/I_B = 20$

Fig 12. Collector-emitter saturation resistance as a function of collector current; typical values

8. Test information

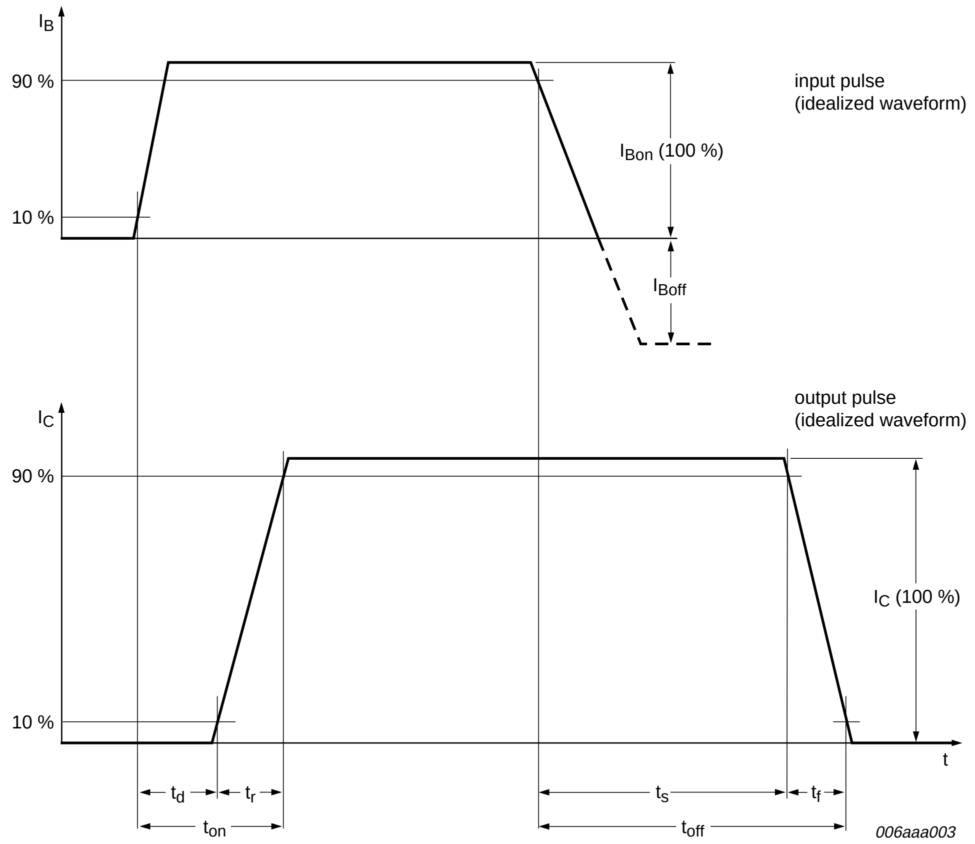
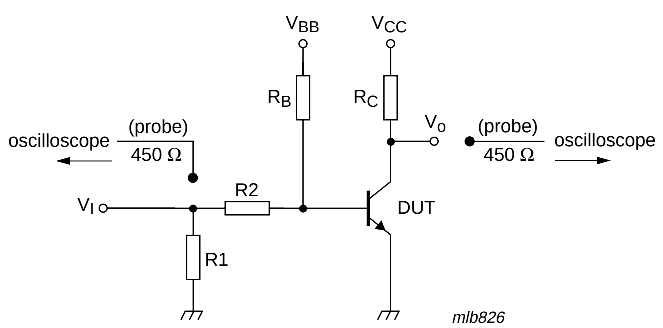


Fig 13. BISS transistor switching time definition



V_{CC} = 10 V; I_C = 0.5 A; I_{Bon} = 0.025 A; I_{Boff} = –0.025 A

Fig 14. Test circuit for switching times

9. Package outline

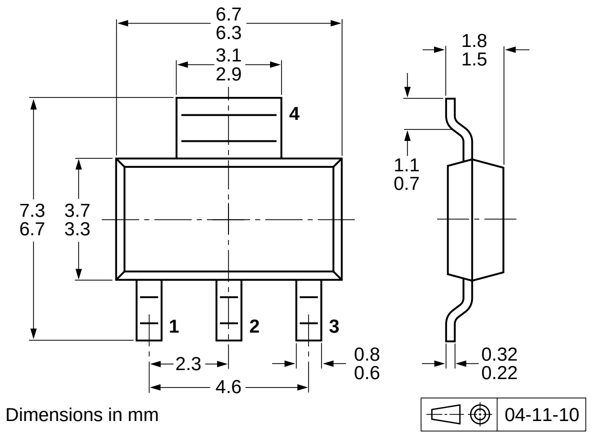


Fig 15. Package outline SOT223 (SC-73)

10. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			1000	4000
PBSS8110Z	SOT223	8 mm pitch, 12 mm tape and reel	-115	-135

[1] For further information and the availability of packing methods, see Section 14.

11. Soldering

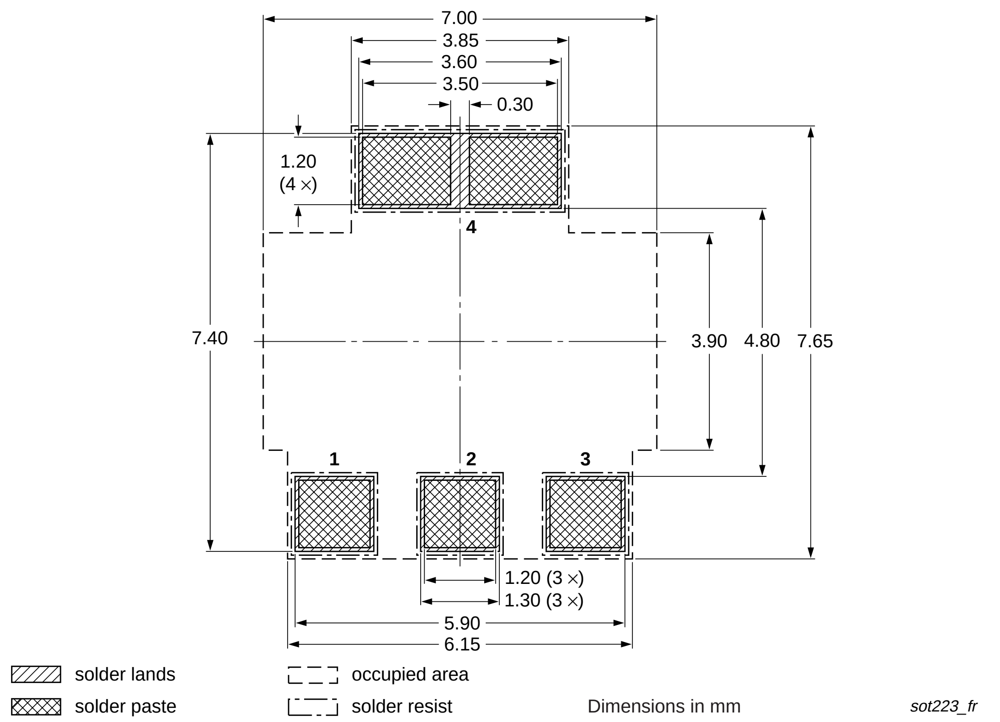


Fig 16. Reflow soldering footprint SOT223 (SC-73)

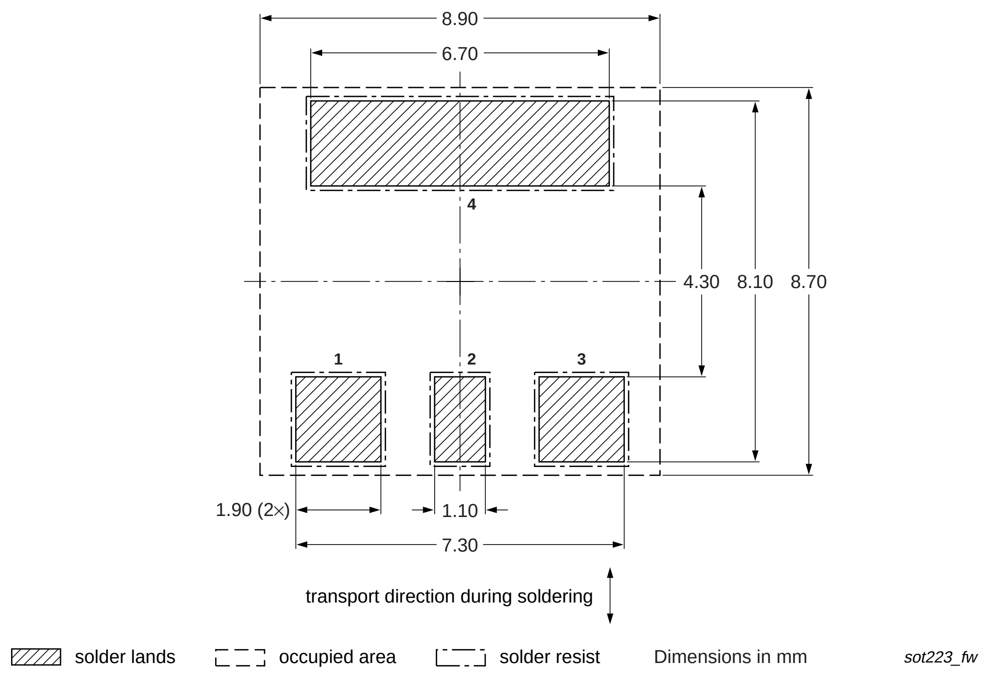


Fig 17. Wave soldering footprint SOT223 (SC-73)

12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS8110Z_2	20070108	Product data sheet	-	PBSS8110Z_1
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Section 1.1 "General description": amended • Section 1.2 "Features": amended • Section 1.3 "Applications": amended • Table 1 "Quick reference data": conditions for I_{CM} peak collector current adapted • Table 1: R_{CEsat} equivalent on-resistance redefined to collector-emitter saturation resistance • Table 2 "Pinning": simplified outline drawing amended • Table 4 "Marking codes": amended • Table 5 "Limiting values": conditions for I_{CM} peak collector current adapted • Table 5: T_{amb} operating ambient temperature redefined to ambient temperature • Table 6 "Thermal characteristics": amended • Table 6: $R_{th(j-s)}$ thermal resistance from junction to soldering point redefined to $R_{th(j-sp)}$ thermal resistance from junction to solder point • Figure 2: amended • Figure 2: Z_{th} transient thermal impedance redefined to $Z_{th(j-a)}$ transient thermal impedance from junction to ambient • Figure 2: t_p pulse time redefined to pulse duration • Figure 3 and 4: added • Table 7: R_{CEsat} equivalent on-resistance redefined to collector-emitter saturation resistance • Table 7: switching times added • Figure 5, 6, 8 and 12: amended • Section 8 "Test information": added • Figure 15: superseded by minimized package outline drawing • Section 10 "Packing information": added • Section 11 "Soldering": added • Section 13 "Legal information": updated			
PBSS8110Z_1	20040426	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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15. Contents

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Date of release: 8 January 2007

Document identifier: PBSS8110Z_2

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